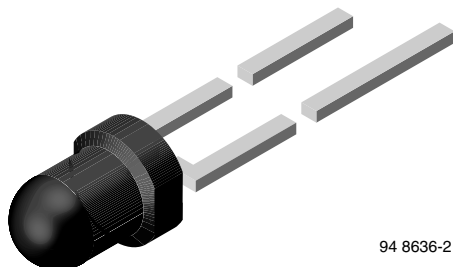


Silicon NPN Phototransistor, RoHS Compliant



94 8636-2

DESCRIPTION

TEFT4300 is a silicon NPN phototransistor with high radiant sensitivity in black, T-1 plastic package with daylight blocking filter. Filter bandwidth is matched with 900 nm to 950 nm IR emitters.

FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm): Ø 3
- High radiant sensitivity
- Daylight blocking filter matched with 940 nm emitters
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 30^\circ$
- Package matched with IR emitter series TSUS4300 and TSAL4400
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

APPLICATIONS

- Optical switches
- Counters and sorters
- Interrupters
- Encoders
- Position sensors

PRODUCT SUMMARY

COMPONENT	I_{ca} (mA)	φ (deg)	$\lambda_{0.5}$ (nm)
TEFT4300	3.2	± 30	875 to 1000

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TEFT4300	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	5	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10$ ms	I_{CM}	100	mA
Power dissipation	$T_{amb} \leq 55^\circ\text{C}$	P_V	100	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 3$ s, 2 mm from case	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R_{thJA}	450	K/W

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

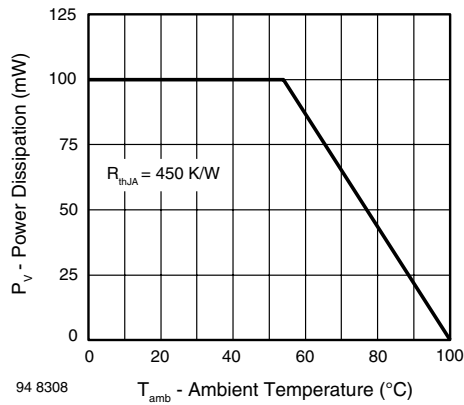


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}$	$V_{(BR)CEO}$	70			V
Collector emitter dark current	$V_{CE} = 20 \text{ V}, E = 0$	I_{CEO}		1	200	nA
Collector emitter capacitance	$V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_{CEO}		3		pF
Collector light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_{CE} = 5 \text{ V}$	I_{ca}	0.8	3.2		mA
Angle of half sensitivity		ϕ		± 30		deg
Wavelength of peak sensitivity		λ_p		925		nm
Range of spectral bandwidth		$\lambda_{0.5}$		875 to 1000		nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, I_C = 0.1 \text{ mA}$	V_{CEsat}			0.3	V
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{on}		2.0		μs
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{off}		2.3		μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	f_c		180		kHz

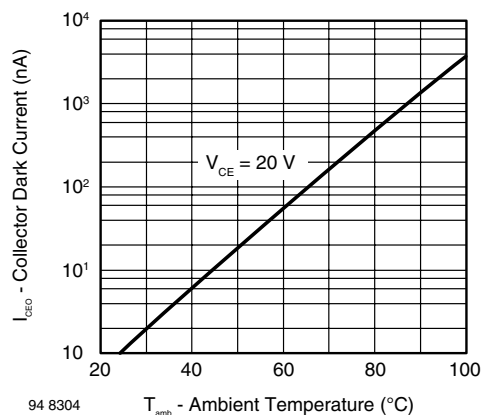
Note $T_{amb} = 25^\circ\text{C}$, unless otherwise specified**BASIC CHARACTERISTICS** $T_{amb} = 25^\circ\text{C}$, unless otherwise specified

Fig. 2 - Collector Dark Current vs. Ambient Temperature

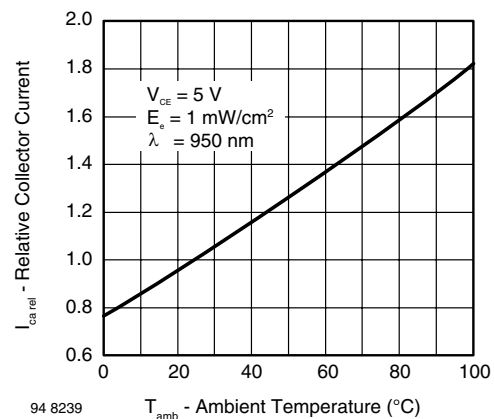


Fig. 3 - Relative Collector Current vs. Ambient Temperature

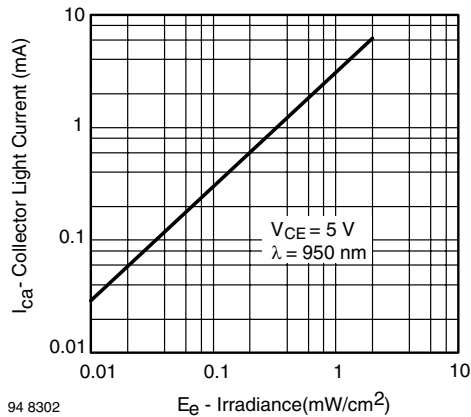


Fig. 4 - Collector Light Current vs. Irradiance

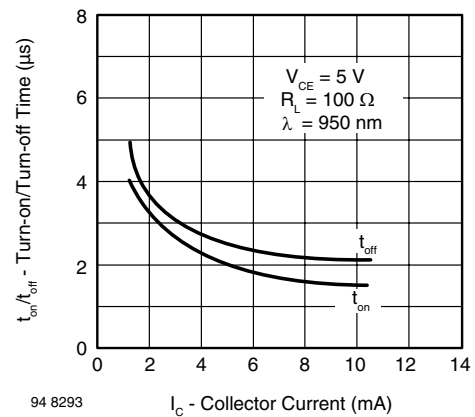


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

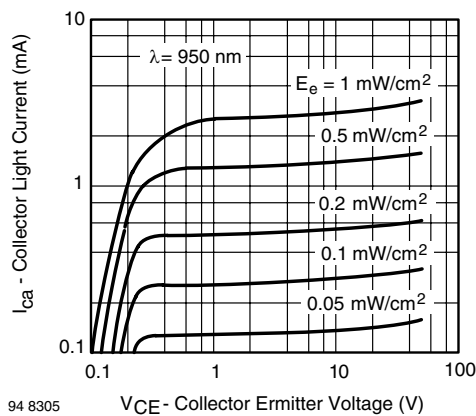


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

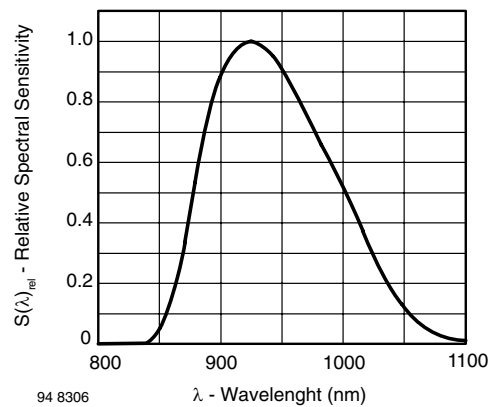


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

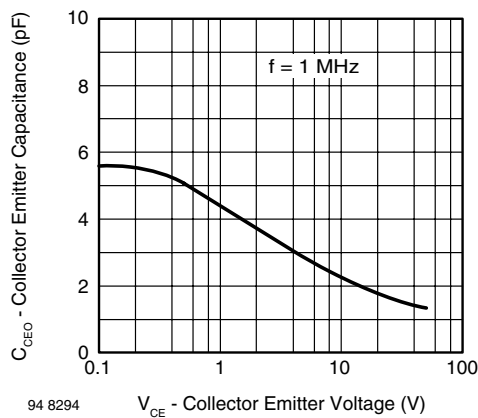


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

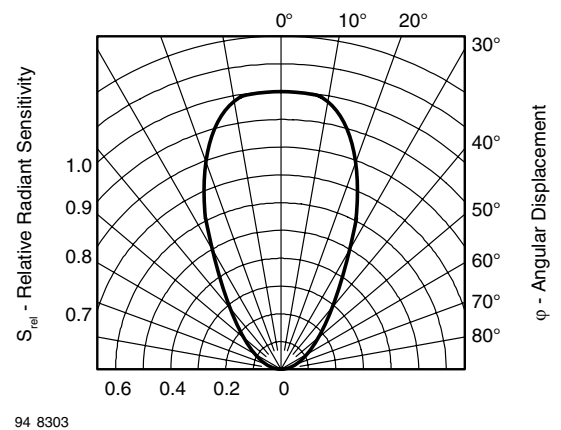
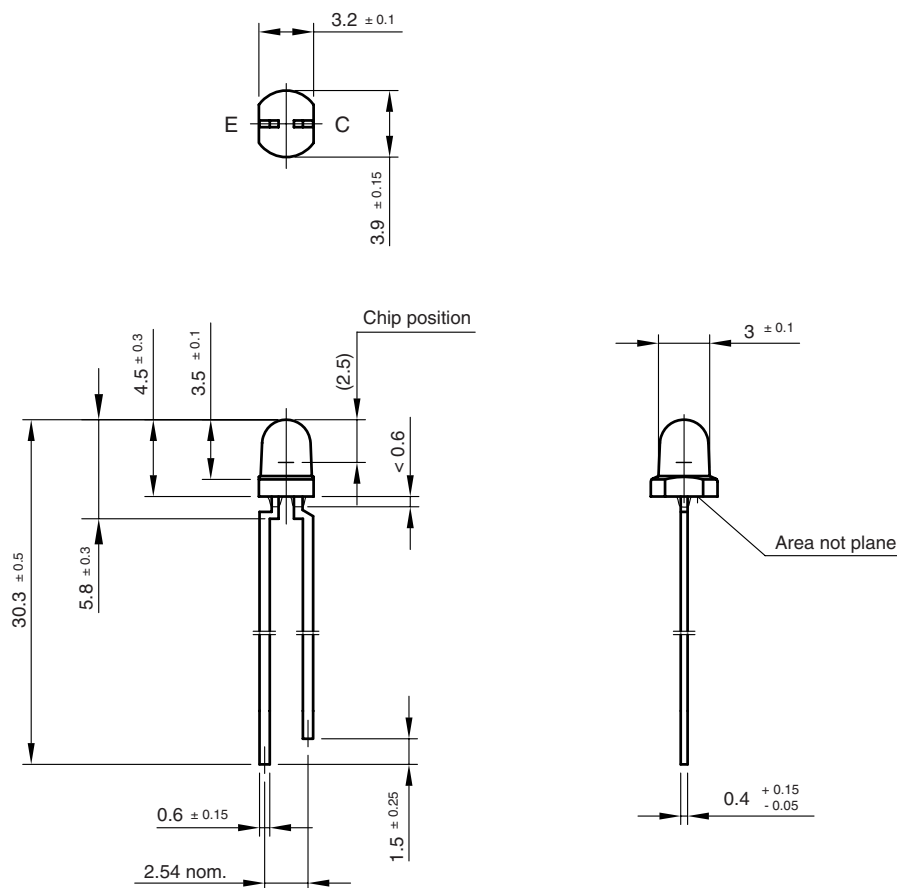


Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



technical drawings
according to DIN
specifications

Drawing-No.: 6.544-5269.01-4

Issue: 4; 01.12.99

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